

## **IN THE CLAIMS**

The following listing of claims replaces all prior listings:

1. (currently amended) A method for manufacturing a micromachine including an oscillator, comprising:

a step of forming a sacrifice layer around a movable portion of the oscillator, the sacrificial layer comprising silicon dioxide;

a step of covering the sacrifice layer with an overcoat film, followed by the formation of a penetrating hole reaching the sacrifice layer in the overcoat layer;

a step of performing sacrifice-layer etching which removes the sacrifice layer using the penetrating hole in order to form a space around the movable portion; and

a step of performing a film-formation treatment by sputtering at a reduced pressure following the sacrifice-layer etching so as to form a sputtering layer that seals the penetrating hole and is formed into a wiring layer at least one wire,

wherein,

the sputtering layer is composed of one selected from the group consisting of an aluminum copper film and an aluminum silicon film.

2. (original) The method for manufacturing a micromachine, according to claim 1, wherein the method is applied to a micromachine having means for driving oscillation in the oscillator.

3. (original) The method for manufacturing a micromachine, according to claim 2, wherein static electricity is used as the means for driving oscillation.

4. (original) The method for manufacturing a micromachine, according to claim 2, wherein piezoelectricity is used as the means for driving oscillation.

5. (original) The method for manufacturing a micromachine, according to claim 1, wherein the film-formation treatment at a reduced pressure is a film-formation treatment by sputtering.